

IN THE SPECIFICATION:

Please amend the Specification as follows:

On Page 1, above the first paragraph and below the title, please amend the previously inserted following paragraphs:

--CROSS REFERENCE TO RELATED APPLICATIONS

Applicants claim priority under 35 U.S.C. §119 of German Patent Application Serial No. 199 09 557.4, filed on March 4, 1999 and German Patent Application Serial No. 100 04 623.1 filed February 3, 2000. Applicants also claim priority under 35 U.S.C. §120 365 of International Application PCT/EP00/01800, filed on March 2, 2000. The International Application under PCT article 21 (2) was not published in English.--

On page 1 between the first paragraph and the second paragraph, please amend the previously inserted following paragraphs:

--2. The Prior Art

EP-829559 A1 discloses a process for producing semiconductor wafers with a low defect density, it being necessary to provide a

single crystal which has to be pulled with forced cooling or has to have a specific oxygen and nitrogen concentration, and semiconductor wafers obtained from the single crystal having to be subjected to heat treatment. EP-644588 A1 relates to a semiconductor wafer having an epitaxially provided layer which has a low defect density and originates from a single crystal pulled at a pulling rate of at most ~~more~~ 0.6 mm/min.--